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# Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	960
Number of Logic Elements/Cells	7680
Total RAM Bits	131072
Number of I/O	93
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	121-VFBGA
Supplier Device Package	121-UCBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp8k-cm121tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Table 1-1. iCE40 Family Selection Guide (continued)	Table 1-1.	iCE40 Famil	y Selection	Guide	(continued)
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84 QFN								
(7 mm x 7 mm, 0.5 mm)	QN84		67(7) <sup>1</sup>					
100 VQFP (14 mm x 14 mm, 0.5 mm)	VQ100					72(9) <sup>1</sup>		
121 ucBGA (5 mm x 5 mm, 0.4 mm)	CM121		95(12)	93(13)	93(13)			
121 csBGA (6 mm x 6 mm, 0.5 mm)	CB121		92(12)					
121 caBGA (9 mm x 9 mm, 0.8 mm)	BG121						93(13)	93(13)
132 csBGA (8 mm x 8 mm, 0.5 mm)	CB132					95(11)	95(12)	95(12)
144 TQFP (20 mm x 20 mm, 0.5 mm)	TQ144					96(12)	107(14)	
225 ucBGA (7 mm x 7 mm, 0.4 mm)	CM225			178(23)	178(23)			178(23)
256-ball caBGA (14 mm x 14 mm, 0.8 mm)	CT256							206(26)

- 1. No PLL available on the 16 WLCSP, 36 ucBGA, 81 csBGA, 84 QFN and 100 VQFP packages.
- 2. Only one PLL available on the 81 ucBGA package.
- 3. High Current I/Os only available on the 16 WLCSP package.

#### Introduction

The iCE40 family of ultra-low power, non-volatile FPGAs has five devices with densities ranging from 384 to 7680 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic, these devices feature Embedded Block RAM (EBR), Non-volatile Configuration Memory (NVCM) and Phase Locked Loops (PLLs). These features allow the devices to be used in low-cost, high-volume consumer and system applications. Select packages offer High-Current drivers that are ideal to drive three white LEDs, or one RGB LED.

The iCE40 devices are fabricated on a 40 nm CMOS low power process. The device architecture has several features such as programmable low-swing differential I/Os and the ability to turn off on-chip PLLs dynamically. These features help manage static and dynamic power consumption, resulting in low static power for all members of the family. The iCE40 devices are available in two versions – ultra low power (LP) and high performance (HX) devices.

The iCE40 FPGAs are available in a broad range of advanced halogen-free packages ranging from the space saving 1.40x1.48 mm WLCSP to the PCB-friendly 20x20 mm TQFP. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The iCE40 devices offer enhanced I/O features such as pull-up resistors. Pull-up features are controllable on a "per-pin" basis.

The iCE40 devices also provide flexible, reliable and secure configuration from on-chip NVCM. These devices can also configure themselves from external SPI Flash or be configured by an external master such as a CPU.

Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the iCE40 family of devices. Popular logic synthesis tools provide synthesis library support for iCE40. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the iCE40 device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) modules, including a number of reference designs, licensed free of charge, optimized for the iCE40 FPGA family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.



#### **Global Reset Control**

The global reset control signal connects to all PLB and PIO flip-flops on the iCE40 device. The global reset signal is automatically asserted throughout the configuration process, forcing all flip-flops to their defined wake-up state. For PLB flip-flops, the wake-up state is always reset, regardless of the PLB flip-flop primitive used in the application.

#### sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The iCE40 devices have one or more sys-CLOCK PLLs. REFERENCECLK is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. EXTFEEDBACK is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The PLLOUT output has an output divider, thus allowing the PLL to generate different frequencies for each output. The output divider can have a value from 1 to 6. The PLLOUT outputs can all be used to drive the iCE40 global clock network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-3.

The timing of the device registers can be optimized by programming a phase shift into the PLLOUT output clock which will advance or delay the output clock with reference to the REFERENCECLK clock. This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t<sub>LOCK</sub> parameter has been satisfied.

For more details on the PLL, see TN1251, iCE40 sysCLOCK PLL Design and Usage Guide.

Figure 2-3. PLL Diagram

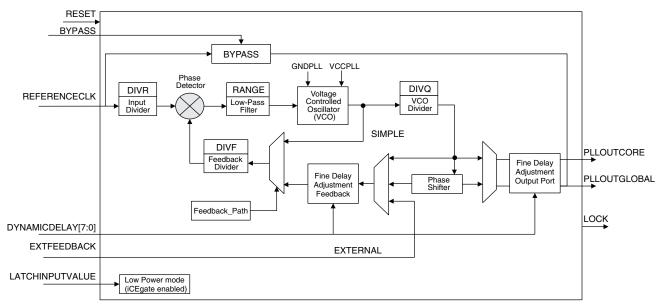


Table 2-3 provides signal descriptions of the PLL block.



#### **RAM Initialization and ROM Operation**

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

#### **Memory Cascading**

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

#### **RAM4k Block**

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

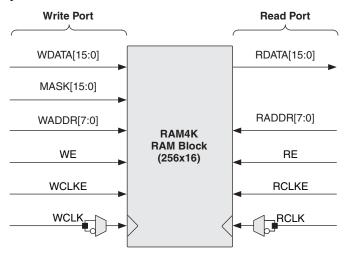


Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines.  0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, Memory Usage Guide for iCE40 Devices.



Figure 2-6. iCE I/O Register Block Diagram

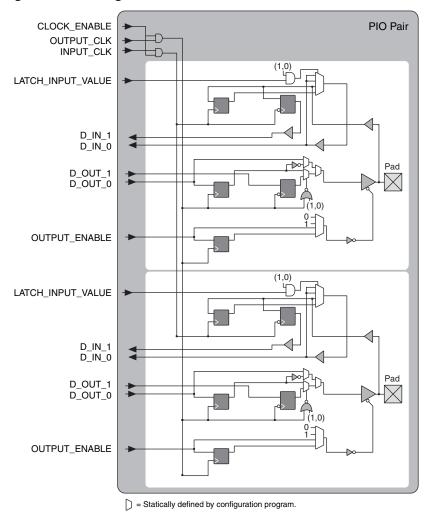


Table 2-6. PIO Signal List

Pin Name	I/O Type	Description
OUTPUT_CLK	Input	Output register clock
CLOCK_ENABLE	Input	Clock enable
INPUT_CLK	Input	Input register clock
OUTPUT_ENABLE	Input	Output enable
D_OUT_0/1	Input	Data from the core
D_IN_0/1	Output	Data to the core
LATCH_INPUT_VALUE	Input	Latches/holds the Input Value

#### sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS and LVDS25.

High Current LED Drivers combine three sysIO buffers together. This allows for programmable drive strength. This also allows for high current drivers that are ideal to drive three white LEDs, or one RGB LED. Each bank is capable of supporting multiple I/O standards including single-ended LVCMOS buffers and differential LVDS25E output buf-



#### **DC Electrical Characteristics**

#### **Over Recommended Operating Conditions**

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
·-, ···	Input or I/O Leakage	$0V < V_{IN} < V_{CCIO} + 0.2 V$	_	_	+/-10	μΑ
C <sub>1</sub> <sup>6, 7</sup>	I/O Capacitance <sup>2</sup>	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}$ $V_{CC} = \text{Typ.}, V_{IO} = 0 \text{ to } V_{CCIO} + 0.2 \text{ V}$	_	6	_	pf
C <sub>2</sub> <sup>6, 7</sup>	Global Input Buffer Capacitance <sup>2</sup>	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}$ $V_{CC} = \text{Typ.}, V_{IO} = 0 \text{ to } V_{CCIO} + 0.2 \text{ V}$	_	6	_	pf
$V_{HYST}$	Input Hysteresis	V <sub>CCIO</sub> = 1.8 V, 2.5 V, 3.3 V	_	200	_	mV
I <sub>PU</sub> <sup>6, 7</sup>	Internal PIO Pull-up	$V_{CCIO} = 1.8 \text{ V}, 0 = < V_{IN} < = 0.65 V_{CCIO}$	-3	_	-31	μΑ
	Current	$V_{CCIO} = 2.5 \text{ V}, 0 = < V_{IN} < = 0.65 V_{CCIO}$	-8	_	-72	μΑ
		$V_{CCIO} = 3.3 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-11		-128	μΑ

- 1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Internal pull-up resistors are disabled.
- 2. T<sub>.1</sub> 25°C, f = 1.0 MHz.
- 3. Please refer to  $V_{IL}$  and  $V_{IH}$  in the sysIO Single-Ended DC Electrical Characteristics table of this document.
- 4. Only applies to IOs in the SPI bank following configuration.
- 5. Some products are clamped to a diode when  $V_{IN}$  is larger than  $V_{CCIO}$ .
- 6. High current IOs has three sysIO buffers connected together.
- 7. The iCE40LP640 and iCE40LP1K SWG16 package has CDONE and a sysIO buffer are connected together.

## Static Supply Current - LP Devices<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typ. V <sub>CC</sub> ⁴	Units
		iCE40LP384	21	μΑ
lcc		iCE40LP640	100	μΑ
	Core Power Supply	iCE40LP1K	100	μΑ
		iCE40LP4K	250	μΑ
		iCE40LP8K	250	μΑ
I <sub>CCPLL</sub> <sup>5, 6</sup>	PLL Power Supply	All devices	0.5	μΑ
I <sub>PP_2V5</sub>	NVCM Power Supply	All devices	1.0	μΑ
I <sub>CCIO,</sub> I <sub>CC_SPI</sub>	Bank Power Supply <sup>4</sup> V <sub>CCIO</sub> = 2.5 V	All devices	3.5	μΑ

Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V<sub>CCIO</sub> or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.

- 2. Frequency = 0 MHz.
- 3.  $T_{J} = 25$  °C, power supplies at nominal voltage.
- 4. Does not include pull-up.
- 5. No PLL available on the iCE40LP384 and iCE40LP640 device.
- 6.  $V_{CCPLL}$  is tied to  $V_{CC}$  internally in packages without PLLs pins.



# Static Supply Current – HX Devices<sup>1, 2, 3, 4</sup>

Symbol Parameter		Device	Typ. V <sub>CC</sub> ⁴	Units	
		iCE40HX1K	296	μΑ	
I <sub>CC</sub>	o and a supply	iCE40HX4K	1140	μΑ	
		iCE40HX8K	1140	μΑ	
I <sub>CCPLL</sub> <sup>5</sup>	PLL Power Supply	All devices	0.5	μΑ	
I <sub>PP_2V5</sub>	NVCM Power Supply	All devices	1.0	μΑ	
Iccio, Icc_spi	Bank Power Supply <sup>4</sup> V <sub>CCIO</sub> = 2.5 V	All devices	3.5	μΑ	

Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V<sub>CCIO</sub> or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.

- 2. Frequency = 0 MHz.
- 3.  $T_J = 25$  °C, power supplies at nominal voltage.
- 4. Does not include pull-up.
- 5.  $V_{\mbox{\footnotesize CCPLL}}$  is tied to  $V_{\mbox{\footnotesize CC}}$  internally in packages without PLLs pins.

# Programming NVCM Supply Current – LP Devices<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typ. V <sub>CC</sub> ⁵	Units
		iCE40LP384	60	μΑ
Icc		iCE40LP640	120	μΑ
	Core Power Supply	iCE40LP1K	120	μΑ
		iCE40LP4K	350	μΑ
		iCE40LP8K	350	μΑ
I <sub>CCPLL</sub> <sup>6, 7</sup>	PLL Power Supply	All devices	0.5	μΑ
I <sub>PP_2V5</sub>	NVCM Power Supply	All devices	2.5	mA
I <sub>CCIO<sup>8</sup>, I<sub>CC_SPI</sub></sub>	Bank Power Supply⁵	All devices	3.5	mA

- 1. Assumes all inputs are held at  $V_{\mbox{\scriptsize CCIO}}$  or GND and all outputs are tri-stated.
- 2. Typical user pattern.
- 3. SPI programming is at 8 MHz.
- 4.  $T_{.1} = 25$  °C, power supplies at nominal voltage.
- 5. Per bank.  $V_{CCIO} = 2.5 \text{ V}$ . Does not include pull-up.
- 6. No PLL available on the iCE40-LP384 and iCE40-LP640 device.
- 7.  $V_{\mbox{\footnotesize CCPLL}}$  is tied to  $V_{\mbox{\footnotesize CC}}$  internally in packages without PLLs pins.
- 8. V<sub>PP\_FAST</sub>, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V<sub>PP\_FAST</sub> ball connected to V<sub>CCIO\_0</sub> ball externally.



# **Peak Startup Supply Current – HX Devices**

Symbol	Parameter	Device	Max	Units
		iCE40HX1K	6.9	mA
I <sub>CCPEAK</sub>	Core Power Supply	iCE40HX4K	22.3	mA
		iCE40HX8K	22.3	mA
		iCE40HX1K 6.9 iCE40HX4K 22.3 iCE40HX8K 22.3 iCE40HX1K 1.8 iCE40HX4K 6.4 iCE40HX8K 6.4 iCE40HX8K 2.8	mA	
I <sub>CCPLLPEAK</sub> <sup>1</sup>	PLL Power Supply	iCE40HX4K	6.4	mA
		iCE40HX8K	6.4	mA
		iCE40HX1K	2.8	mA
I <sub>PP_2V5PEAK</sub>	NVCM Power Supply	iCE40HX4K	4.1	mA
		iCE40HX8K	4.1	mA
		iCE40HX1K	6.8	mA
ICCIOPEAK, ICC_SPIPEAK	ICE40HX1K   6.9	mA		
		iCE40HX8K	6.8	mA

<sup>1.</sup>  $\rm V_{CCPLL}$  is tied to  $\rm V_{CC}$  internally in packages without PLLs pins.

## sysIO Recommended Operating Conditions

	V <sub>CCIO</sub> (V)					
Standard	Min.	Тур.	Max.			
LVCMOS 3.3	3.14	3.3	3.46			
LVCMOS 2.5	2.37	2.5	2.62			
LVCMOS 1.8	1.71	1.8	1.89			
LVDS25E <sup>1, 2</sup>	2.37	2.5	2.62			
subLVDSE <sup>1, 2</sup>	1.71	1.8	1.89			

<sup>1.</sup> Inputs on-chip. Outputs are implemented with the addition of external resistors.

## sysIO Single-Ended DC Electrical Characteristics

Input/	V <sub>IL</sub>		V <sub>IH</sub> <sup>1</sup>			\/ B#1			
Output Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	V <sub>OL</sub> Max. (V)	V <sub>OH</sub> Min. (V)	I <sub>OL</sub> Max. (mA)	I <sub>OH</sub> Max. (mA)	
LVCMOS 3.3	-0.3	0.8 2.0	2.0	2.0 V <sub>CCIO</sub> + 0.2 V	0.4	V <sub>CCIO</sub> - 0.4	8, 16 <sup>2</sup> , 24 <sup>2</sup>	$-8, -16^2, -24^2$	
LV OIVIOU 3.5	0.0		2.0		Z.O VCCIO 1 O.Z V	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	V + 0.2 V	0.4	V <sub>CCIO</sub> - 0.4	6, 12 <sup>2</sup> , 18 <sup>2</sup>	$-6, -12^2, -18^2$	
LV CIVIOS 2.5	-0.3	0.7	1.7 V <sub>CCIO</sub> + 0.2 V	0.7	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
LVCMOS 1.8	-0.3	0.051/	0.251/	0.65V <sub>CCIO</sub>	:5V V + 0.2 V	0.4	V <sub>CCIO</sub> - 0.4	4, 8 <sup>2</sup> , 12 <sup>2</sup>	$-4, -8^2, -12^2$
LVCIVIOS 1.8	-0.5	0.35V <sub>CCIO</sub>	0.03 V CCIO	V <sub>CCIO</sub> + 0.2 V	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	

<sup>1.</sup> Some products are clamped to a diode when  $V_{\text{IN}}$  is larger than  $V_{\text{CCIO.}}$ 

<sup>2.</sup> Does not apply to Configuration Bank V<sub>CC SPI</sub>.

<sup>2.</sup> Only for High Drive LED outputs.



# sysIO Differential Electrical Characteristics

The LVDS25E/subLVDSE differential output buffers are available on all banks but the LVDS/subLVDS input buffers are only available on Bank 3 of iCE40 devices.

#### LVDS25

#### **Over Recommended Operating Conditions**

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
$V_{INP}$ , $V_{INM}$	Input Voltage	$V_{\text{CCIO}}^{1} = 2.5$	0		2.5	V
$V_{THD}$	Differential Input Threshold		250	350	450	mV
$V_{CM}$	Input Common Mode Voltage	$V_{CCIO}^{1} = 2.5$	(V <sub>CCIO</sub> /2) - 0.3	V <sub>CCIO</sub> /2	$(V_{CCIO}/2) + 0.3$	V
I <sub>IN</sub>	Input Current	Power on		1	±10	μΑ

<sup>1.</sup> Typical.

#### **subLVDS**

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
V <sub>INP,</sub> V <sub>INM</sub>	Input Voltage	$V_{\text{CCIO}}^{1} = 1.8$	0	_	1.8	V
$V_{THD}$	Differential Input Threshold		100	150	200	mV
V <sub>CM</sub>	Input Common Mode Voltage	$V_{\text{CCIO}}^{1} = 1.8$	(V <sub>CCIO</sub> /2) - 0.25	V <sub>CCIO</sub> /2	$(V_{CCIO}/2) + 0.25$	V
I <sub>IN</sub>	Input Current	Power on	_	_	±10	μΑ

<sup>1.</sup> Typical.



#### LVDS25E Emulation

iCE40 devices can support LVDSE outputs via emulation on all banks. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS25E standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS25E Using External Resistors

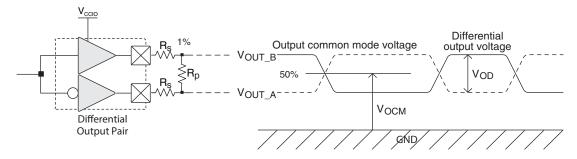


Table 3-1. LVDS25E DC Conditions

Parameter	Description	Тур.	Units
Z <sub>OUT</sub>	Output impedance	20	Ohms
R <sub>S</sub>	Driver series resistor	150	Ohms
R <sub>P</sub>	Driver parallel resistor	140	Ohms
R <sub>T</sub>	Receiver termination	100	Ohms
V <sub>OH</sub>	Output high voltage	1.43	V
V <sub>OL</sub>	Output low voltage	1.07	V
V <sub>OD</sub>	Output differential voltage	0.30	V
V <sub>CM</sub>	Output common mode voltage	1.25	V
Z <sub>BACK</sub>	Back impedance	100.5	Ohms
I <sub>DC</sub>	DC output current	6.03	mA



#### **SubLVDS Emulation**

The iCE40 family supports the differential subLVDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all banks of the devices. The subLVDS input standard is supported by the LVDS25 differential input buffer. The scheme shown in Figure 3-2 is one possible solution for subLVDSE output standard implementation. Use LVDS25E mode with suggested resistors for subLVDSE operation. Resistor values in Figure 3-2 are industry standard values for 1% resistors.

Figure 3-2. subLVDSE

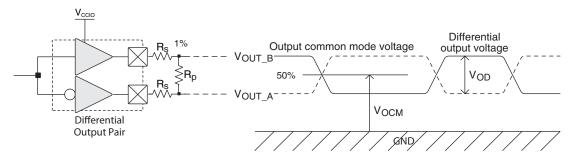


Table 3-2. subLVDSE DC Conditions

Parameter	Description	Тур.	Units
Z <sub>OUT</sub>	Output impedance	20	Ohms
R <sub>S</sub>	Driver series resistor	270	Ohms
R <sub>P</sub>	Driver parallel resistor	120	Ohms
R <sub>T</sub>	Receiver termination	100	Ohms
V <sub>OH</sub>	Output high voltage	1.43	V
V <sub>OL</sub>	Output low voltage	1.07	V
$V_{OD}$	Output differential voltage	0.35	V
V <sub>CM</sub>	Output common mode voltage	0.9	V
Z <sub>BACK</sub>	Back impedance	100.5	Ohms
I <sub>DC</sub>	DC output current	2.8	mA



## **Derating Logic Timing**

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

## Maximum sysIO Buffer Performance<sup>2</sup>

I/O Standard	Max. Speed	Units
	Inputs	
LVDS25 <sup>1</sup>	400	MHz
subLVDS18 <sup>1</sup>	400	MHz
LVCMOS33	250	MHz
LVCMOS25	250	MHz
LVCMOS18	250	MHz
	Outputs	
LVDS25E	250	MHz
subLVDS18E	155	MHz
LVCMOS33	250	MHz
LVCMOS25	250	MHz
LVCMOS18	155	MHz

<sup>1.</sup> Supported in Bank 3 only.

### iCE40 Family Timing Adders

## Over Recommended Commercial Operating Conditions - LP Devices<sup>1, 2, 3, 4, 5</sup>

Buffer Type	Description	Timing	Units
Input Adjusters			
LVDS25	LVDS, V <sub>CCIO</sub> = 2.5 V	-0.18	ns
subLVDS	subLVDS, V <sub>CCIO</sub> = 1.8 V	0.82	ns
LVCMOS33	LVCMOS, V <sub>CCIO</sub> = 3.3 V	0.18	ns
LVCMOS25	LVCMOS, V <sub>CCIO</sub> = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V <sub>CCIO</sub> = 1.8 V	0.19	ns
Output Adjusters	·		
LVDS25E	LVDS, Emulated, V <sub>CCIO</sub> = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V <sub>CCIO</sub> = 1.8 V	1.32	ns
LVCMOS33	LVCMOS, V <sub>CCIO</sub> = 3.3 V	-0.12	ns
LVCMOS25	LVCMOS, V <sub>CCIO</sub> = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V <sub>CCIO</sub> = 1.8 V	1.32	ns

- 1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.
- 2. LVCMOS timing measured with the load specified in Switching Test Condition table.
- 3. All other standards tested according to the appropriate specifications.
- 4. Commercial timing numbers are shown.
- 5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.

<sup>2.</sup> Measured with a toggling pattern



# iCE40 External Switching Characteristics – LP Devices (Continued)<sup>1, 2</sup>

Parameter	Description	Device	Min.	Max.	Units
tHPLL	Clock to Data Hold - PIO Input Register	iCE40LP1K	-0.90	_	ns
		iCE40LP4K	-0.80	_	ns
		iCE40LP8K	-0.80	_	ns

<sup>1.</sup> Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.

<sup>2.</sup> General I/O timing numbers based on LVCMOS 2.5, 0pf load.

<sup>3.</sup> Supported on devices with a PLL.



## sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min.	Max.	Units
f <sub>IN</sub>	Input Clock Frequency (REFERENCECLK, EXTFEEDBACK)		10	133	MHz
f <sub>OUT</sub>	Output Clock Frequency (PLLOUT)		16	275	MHz
$f_{VCO}$	PLL VCO Frequency		533	1066	MHz
f <sub>PFD</sub>	Phase Detector Input Frequency		10	133	MHz
AC Characterist	tics		•		
	Output Clock Duty Cycle	f <sub>OUT</sub> < 175 MHz	40	50	%
t <sub>DT</sub>	Output Clock Duty Cycle	175 MHz < f <sub>OUT</sub> < 275 MHz	35	65	"%
t <sub>PH</sub>	Output Phase Accuracy		_	+/-12	deg
	Output Clock Period Jitter	f <sub>OUT</sub> <= 100 MHz	_	450	ps p-p
	Output Clock Period Sitter	f <sub>OUT</sub> > 100 MHz	_	0.05	UIPP
<b>1</b> , 5	Output Clock Cycle-to-cycle Jitter	f <sub>OUT</sub> <= 100 MHz	_	750	ps p-p
t <sub>OPJIT</sub> 1, 5	Output Clock Cycle-to-cycle Sitter	f <sub>OUT</sub> > 100 MHz	_	0.10	UIPP
	Output Clock Phase litter	f <sub>PFD</sub> <= 25 MHz	_	275	ps p-p
	Output Clock Phase Jitter	f <sub>PFD</sub> > 25 MHz	_	0.05	UIPP
t <sub>W</sub>	Output Clock Pulse Width	At 90% or 10%	1.3	_	ns
t <sub>LOCK</sub> <sup>2, 3</sup>	PLL Lock-in Time		_	50	us
t <sub>UNLOCK</sub>	PLL Unlock Time		_	50	ns
+ 4	Input Clock Period Jitter	f <sub>PFD</sub> ≥ 20 MHz	_	1000	ps p-p
t <sub>IPJIT</sub> <sup>4</sup>	Input Clock Feriod Sitter	f <sub>PFD</sub> < 20 MHz	_	0.02	UIPP
t <sub>FDTAP</sub>	Fine Delay adjustment, per Tap		147	195	ps
t <sub>STABLE</sub> <sup>3</sup>	LATCHINPUTVALUE LOW to PLL Stable		_	500	ns
t <sub>STABLE_PW</sub> <sup>3</sup>	LATCHINPUTVALUE Pulse Width		_	100	ns
t <sub>RST</sub>	RESET Pulse Width		10	_	ns
t <sub>RSTREC</sub>	RESET Recovery Time		10	_	us
t <sub>DYNAMIC_WD</sub>	DYNAMICDELAY Pulse Width		100	_	VCO Cycles
+	Propagation delay with the PLL in bypass	iCE40LP	1.18	4.68	ns
t <sub>PDBYPASS</sub>	mode	iCE40HX	1.73	4.07	ns

<sup>1.</sup> Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.

<sup>2.</sup> Output clock is valid after  $t_{\mbox{\scriptsize LOCK}}$  for PLL reset and dynamic delay adjustment.

<sup>3.</sup> At minimum  $f_{\text{PFD}}$ . As the  $f_{\text{PFD}}$  increases the time will decrease to approximately 60% the value listed.

<sup>4.</sup> Maximum limit to prevent PLL unlock from occurring. Does not imply the PLL will operate within the output specifications listed in this table.

<sup>5.</sup> The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.



# SPI Master or NVCM Configuration Time<sup>1, 2</sup>

Symbol	Parameter	Conditions	Тур.	Units
		iCE40LP384 - Low Frequency (Default)	25	ms
		iCE40LP384 - Medium Frequency	15	ms
		iCE40LP384 - High Frequency	11	ms
		iCE40LP640 - Low Frequency (Default)	53	ms
		iCE40LP640 - Medium Frequency	25	ms
		iCE40LP640 - High Frequency	13	ms
	DOD/ODEOET D	iCE40LP/HX1K - Low Frequency (Default)	53	ms
t <sub>CONFIG</sub>	POR/CRESET_B to Device I/O Active	iCE40LP/HX1K - Medium Frequency	25	ms
		iCE40LP/HX1K - High Frequency	13	ms
		iCE40LP/HX4K - Low Frequency (Default)	230	ms
		iCE40LP/HX4K - Medium Frequency	110	ms
		iCE40LP/HX4K - High Frequency	70	ms
		iCE40LP/HX8K - Low Frequency (Default)	230	ms
		iCE40LP/HX8K - Medium Frequency	110	ms
		iCE40LP/HX8K - High Frequency	70	ms

<sup>1.</sup> Assumes sysMEM Block is initialized to an all zero pattern if they are used.

<sup>2.</sup> The NVCM download time is measured with a fast ramp rate starting from the maximum voltage of POR trip point.



# sysCONFIG Port Timing Specifications<sup>1</sup> (Continued)

Symbol	Parameter		Min.	Тур.	Max.	Units
	Parameter	iCE40LP384 - Low Frequency (Default)	600	_	_	us
		iCE40LP384 - Medium Frequency	600	_	_	us
		iCE40LP384 - High Frequency	600	_	_	us
		iCE40LP640, iCE40LP/HX1K - Low Frequency (Default)	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - Medium Frequency	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - High Frequency	800	_	_	us
	CRESET_B high to first MCLK	iCE40LP/HX1K -Low Frequency (Default)	800	_	_	us
MCLK	edge	iCE40LP/HX1K - Medium Frequency	800	_	_	us
		iCE40LP/HX1K - High Frequency	800	_	_	us
		iCE40LP/HX4K - Low Frequency (Default)	1200	_	_	us
		iCE40LP/HX4K - Medium Frequency	1200	_	_	us
		iCE40LP/HX4K - high frequency	1200	_	_	us
		iCE40LP/HX8K - Low Frequency (Default)	1200	_	_	us
		iCE40LP/HX8K - Medium Frequency	1200	_	_	us
		iCE40LP/HX8K - High Frequency	1200	_	_	us

Does not apply for NVCM.
 Supported only with 1.2 V V<sub>CC</sub> and at 25 °C.
 Extended range f<sub>MAX</sub> Write operations support up to 53 MHz only with 1.2 V V<sub>CC</sub> and at 25 °C.



# **Signal Descriptions (Continued)**

Signal Name	I/O	Descriptions
VPP_FAST	_	Optional fast NVCM programming supply. $V_{PP\_FAST}$ , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the $V_{PP\_FAST}$ ball connected to $V_{CCIO\_0}$ ball externally.
VPP_2V5	_	VPP_2V5 NVCM programming and operating supply

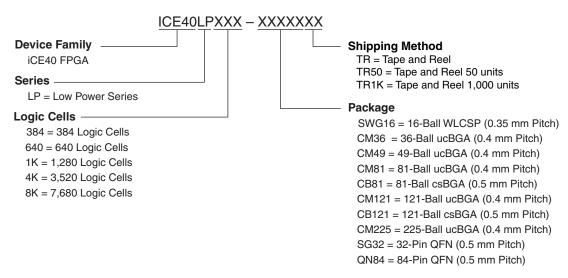


# iCE40 LP/HX Family Data Sheet Ordering Information

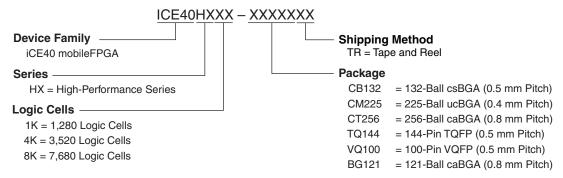
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# iCE40 Part Number Description

#### **Ultra Low Power (LP) Devices**



#### **High Performance (HX) Devices**



All parts shipped in trays unless noted.

## Ordering Information

iCE40 devices have top-side markings as shown below:

#### Industrial



Note: Markings are abbreviated for small packages.

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Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP8K-CM121TR1K	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND

## High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40HX1K-CB132	1280	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX1K-VQ100	1280	1.2 V	Halogen-Free VQFP	100	IND
ICE40HX1K-TQ144	1280	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX4K-BG121	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-BG121TR	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-CB132	3520	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX4K-TQ144	3520	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX8K-BG121	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-BG121TR	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-CB132	7680	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND
ICE40HX8K-CT256	7680	1.2 V	Halogen-Free caBGA	256	IND



# iCE40 LP/HX Family Data Sheet Supplemental Information

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#### For Further Information

A variety of technical notes for the iCE40 family are available on the Lattice web site.

- TN1248, iCE40 Programming and Configuration
- TN1250, Memory Usage Guide for iCE40 Devices
- TN1251, iCE40 sysCLOCK PLL Design and Usage Guide
- TN1252, iCE40 Hardware Checklist
- TN1253, Using Differential I/O (LVDS, Sub-LVDS) in iCE40 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- iCE40 Pinout Files
- Thermal Management document
- Lattice design tools
- IBIS
- Package Diagrams Data Sheet
- Schematic Symbols



# iCE40 LP/HX Family Data Sheet Revision History

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Date	Version	Section	Change Summary	
March 2017 3.3	3.3	Introduction	Updated Features section. Added 121-ball caBGA package for ICE40 HX4K/8K to Table 1-1, iCE40 Family Selection Guide.	
		Architecture	Updated PLB Blocks section. Changed "subtracters" to "subtractors" in the Carry Logic description.	
			Updated Clock/Control Distribution Network section. Switched the "Clock Enable" and the "Reset" headings in Table 2-2, Global Buffer (GBUF) Connections to Programmable Logic Blocks.	
		Pinout Information	Updated Pin Information Summary section. Added BG121information under iCE40HX4K and iCE40HX8K.	
		Ordering Information	Updated iCE40 Part Number Description section. Added Shipping Method and BG121 package under High Performance (HX) Devices.	
			Updated Ordering Information section. Added part numbers for BG121 under High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging.	
	Supplemental Information	Corrected reference to "Package Diagrams Data Sheet".		
October 2015 3.	3.2	Introduction	Updated Features section. Added footnote to 16 WLCSP Programmable I/O: Max Inputs (LVDS25) in Table 1-1, iCE40 Family Selection Guide.	
		DC and Switching Characteristics	Updated sysCLOCK PLL Timing section. Changed t <sub>DT</sub> conditions.	
			Updated Programming NVCM Supply Current – LP Devices section. Changed I <sub>PP_2V5</sub> and I <sub>CCIO</sub> , I <sub>CC_SPI</sub> units.	
March 2015	3.1	DC and Switching Characteristics	Updated sysIO Single-Ended DC Electrical Characteristics section. Changed LVCMOS 3.3 and LVCMOS 2. 5 V <sub>OH</sub> Min. (V) from 0.5 to 0.4.	
July 2014	3.0	DC and Switching Characteristics	Revised and/or added Typ. V <sub>CC</sub> data in the following sections.  — Static Supply Current – LP Devices  — Static Supply Current – HX Devices  — Programming NVCM Supply Current – LP Devices  — Programming NVCM Supply Current – HX Devices  In each section table, the footnote indicating Advanced device status was removed.	
		Pinout Information	Updated Pin Information Summary section. Added footnote 1 to CM49 under iCE40LP1K.	
April 2014	02.9	Ordering Information	Changed "i" to "I" in part number description and ordering part numbers.	
			Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.	